International Rectifier

MBRS320TRPbF

SCHOTTKY RECTIFIER

3 Amp

 $I_{F(AV)} = 3.0 Amp$ $V_R = 20 V$

Major Ratings and Characteristics

Characteristics	Value	Units	
I _{F(AV)} Rectangular waveform	3.0	Α	
V _{RRM}	20	V	
I _{FSM} @t _p =5μs sine	820	Α	
V _F @3.0 Apk, T _J = 125°C	0.36	V	
T _J range	- 65 to 150	°C	

Description/ Features

The MBRS320TRPbF surface-mount Schottky rectifier has been designed for applications requiring low forward drop and small foot prints on PC boards. Typical applications are in disk drives, switching power supplies, converters, free-wheeling diodes, battery charging, and reverse battery protection.

- Small foot print, surface mountable
- Very low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Lead-Free ("PbF" suffix)



Voltage Ratings

Part number	MBRS320PbF	
V _R Max. DC Reverse Voltage (V)	20	
V _{RWM} Max. Working Peak Reverse Voltage (V)	20	

Absolute Maximum Ratings

	Parameters	Value	Units	Conditions	
I _{F(AV)}	Max. Average Forward Current	3.0	Α	50% duty cycle @ T _L = 136°C,	rectangular wave form
I _{FSM}	Max. Peak One Cycle Non-Repetitive	820		5μs Sine or 3μs Rect. pulse	Following any rated load condition and
	Surge Current	80		10ms Sine or 6ms Rect. pulse	with rated V _{RRM} applied
E _{AS}	Non Repetitive Avalanche Energy	4	mJ	$T_J = 25 ^{\circ}\text{C}, I_{AS} = 1.0\text{A}, L = 8\text{mH}$	
I _{AR}	Repetitive Avalanche Current	1.0	А	Current decaying linearly to zero in 1 µsec Frequency limited by T _J max. Va = 1.5 x Vr typical	

Electrical Specifications

	Parameters	Тур.	Max.	Units	Conditio	ns
V _{FM}	Max. Forward Voltage Drop (1)	0.41	0.45	V	@ 3A	T = 25 °C
		0.45	0.53	V	@ 6A	T _J = 25 °C
		0.29	0.36	V	@ 3A	T = 125 °C
		0.35	0.46	V	@ 6A	T _J = 125 °C
I _{RM}	Max. Reverse Leakage Current (1)	0.04	0.5	mA	T _J = 25 °C	
		8.0	20	mA	T _J = 100 °C	V _R = rated V _R
		23	35	mA	T _J = 125 °C	
C _T	Typical Junction Capacitance	360	-	pF	V _R = 5V _{DC} (test signal range 100kHz to	
					1Mhz), @ 25°	С
L _S	Typical Series Inductance	3.0	-	nH	Measured lead to lead 5mm from package body	
dv/dt	Max. Voltage Rate of Change	-	10000	V/ µs	(Rated V _R)	

⁽¹⁾ Pulse Width < 300µs, Duty Cycle < 2%

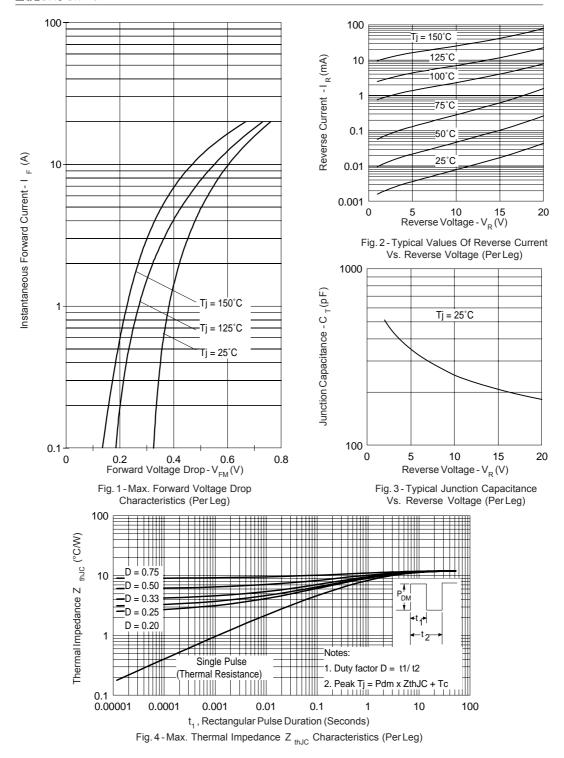
Thermal-Mechanical Specifications

	Parameters	Value	Units	Conditions
T _J	Max. Junction Temperature Range (*)	- 65 to 150	°C	
T _{stg}	Max. Storage Temperature Range	-65 to 150	°C	
R _{thJL}	Max. Thermal Resistance Junction to Lead (**)	12	°C/W	DC operation
R _{thJA}	Max. Thermal Resistance Junction	46	°C/W	
	to Ambient			
Wt	Approximate Weight	0.24(0.008)	gr (oz)	
	Case Style	SMC		Similar DO-214AB
	Device Marking	IR32		

 $[\]frac{\text{(*)}}{\text{dTj}} < \frac{1}{\text{Rth(j-a)}} \quad \text{thermal runaway condition for a diode on its own heatsink}$

^(**) Mounted 1 inch square PCB

Bulletin PD-20410 07/04



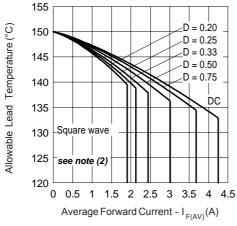


Fig. 5 - Maximum Average Forward Current Vs. Allowable Lead Temperature

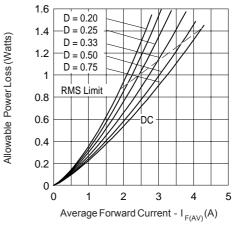


Fig. 6 - Maximum Average Forward Dissipation Vs. Average Forward Current

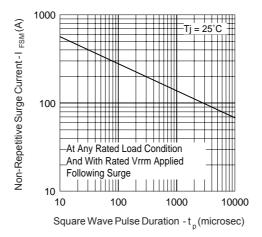
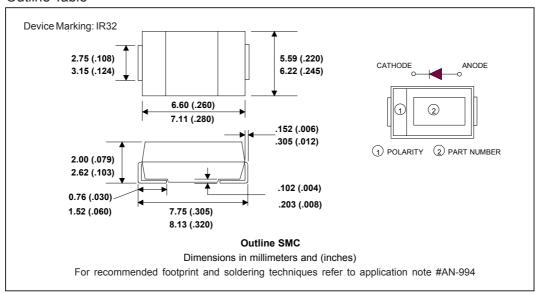


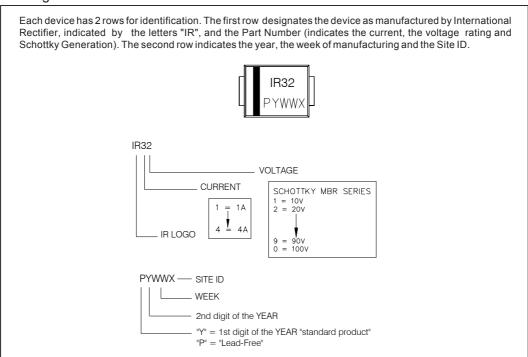
Fig. 7 - Maximum Peak Surge Forward Current Vs. Pulse Duration

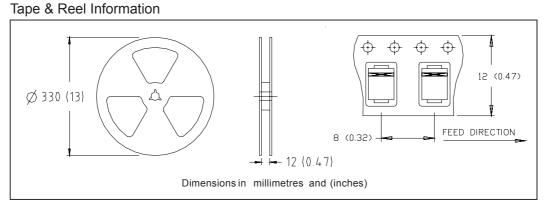
(2) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; $Pd = Forward Power Loss = I_{F(AV)} \times V_{FM} @ (I_{F(AV)} / D)$ (see Fig. 6); $Pd_{REV} = Inverse Power Loss = V_{R1} \times I_R (1 - D)$

Outline Table

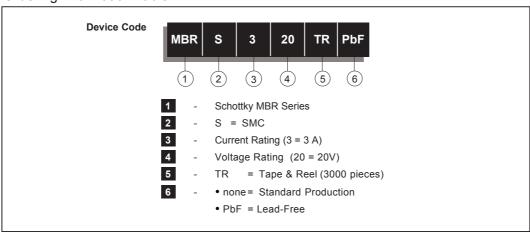


Marking & Identification





Ordering Information Table



Data and specifications subject to change without notice. This product has been designed and qualified for Industrial Level and Lead-Free. Qualification Standards can be found on IR's Web site.



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